



# YJB100GP06H

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## P-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	-60 V
$I_D$	-100 A
$R_{DS(ON)}$ ( at $V_{GS}=-10V$ )	8.8m
$R_{DS(ON)}$ ( at $V_{GS}=-6V$ )	10m
100% EAS Tested.1	



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## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max
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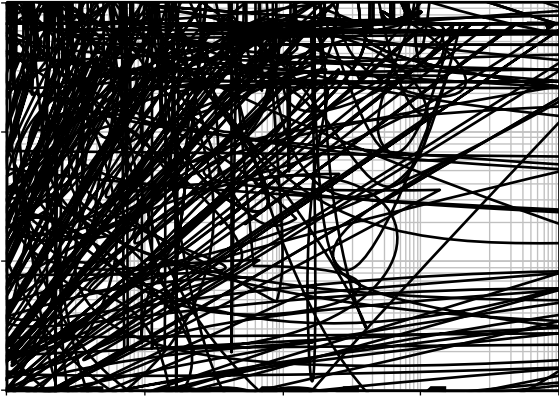
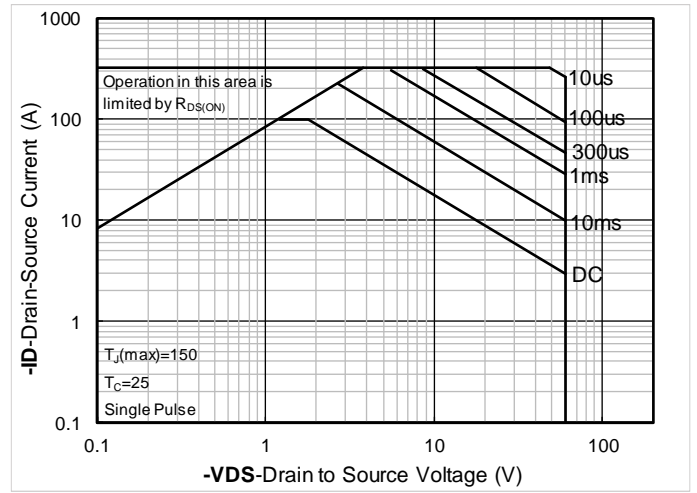


Figure 13. Maximum Transient Thermal Impedance



Figure



TO-263-HY Package information

SYM.	MIN.
A2	
b2	0.050
c	
c2	
D2	
E	
E1	



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